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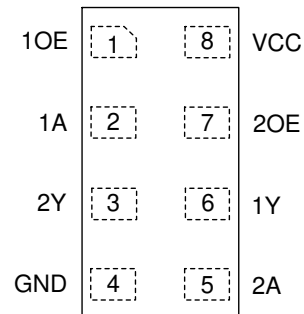


Description

The 74LVC2G126 is a dual buffer gate with 3-state outputs. The device is designed for operation over a power supply range of 1.65V to 5.5V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing damaging current backflow when the device is powered down.

Pin Assignments

(Top View)



X2-DFN2010-8
X2-DFN1410-8
X2-DFN1210-8

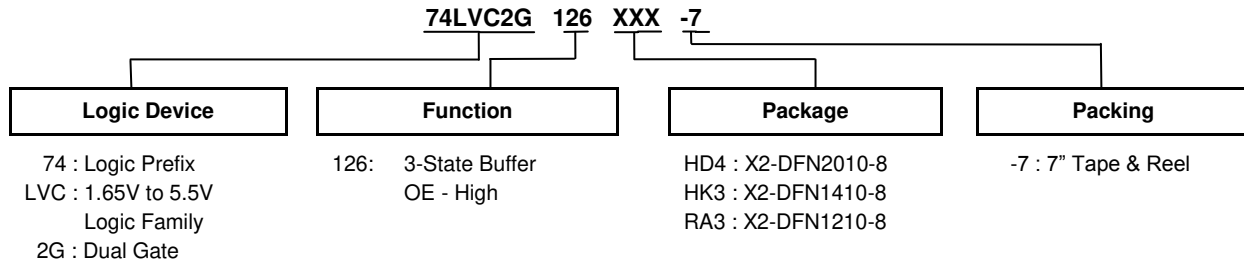
Features

- Wide Supply Voltage Range from 1.65 to 5.5V
- $\pm 24\text{mA}$ Output Drive at 3.3V
- CMOS Low Power Consumption
- I_{OFF} Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall times. The hysteresis is typically 100mV at $V_{CC} = 3.0\text{V}$.
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide Array of Products Such as:
 - PCs, Networking, Notebooks, Netbooks, PDAs
 - Tablet Computers, E-readers
 - Computer Peripherals, Hard Drives, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set Top Boxes
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

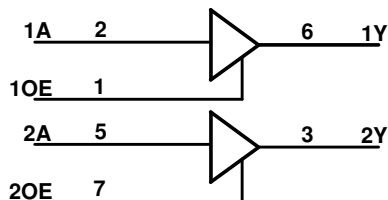
Ordering Information (Note 4)


Device	Package Code	Package (Note 5)	Package Size	7" Tape and Reel (Note 6)	
				Quantity	Part Number Suffix
74LVC2G126HD4-7	HD4	X2-DFN2010-8	1.95mm x 1.0mm x 0.4mm 0.5 mm lead pitch	5,000/Tape & Reel	-7
74LVC2G126HK3-7	HK3	X2-DFN1410-8	1.35mm x 1.0mm x 0.35mm 0.4 mm lead pitch	5,000/Tape & Reel	-7
74LVC2G126RA3-7	RA3	X2-DFN1210-8	1.2mm x 1.0mm x 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7

- Notes: 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.
5. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at <http://www.diodes.com/package-outlines.html>.
6. The taping orientation is located on our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Pin Descriptions

Pin Name	Pin No.	Description
1OE	1	Output Enable for buffer 1
1A	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
1Y	6	Data Output
2OE	7	Output Enable for buffer 2
V _{CC}	8	Supply Voltage

Logic Diagram

Function Table

Inputs		Output
OE	A	Y
H	H	H
H	L	L
L	X	Z

Absolute Maximum Ratings (Notes 7 & 8)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V _{CC}	Supply Voltage	-0.5 to +6.5	V
V _I	Input Voltage	-0.5 to +6.5	V
V _O	Output Voltage - Active Mode	-0.5 to V _{CC} +0.5	V
	Output Voltage Power Down Mode	-0.5 to +6.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
I _{OK}	Output Clamp Current (V _O < 0 OR V _O > V _{CC})	±50	mA
I _O	Continuous Output Current (V _O = 0 to V _{CC})	±50	mA
I _{CC}	Continuous Current Through V _{CC}	100	mA
I _{GND}	Continuous Current Through GND	-100	mA
T _J	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

- Notes:
- Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.
 - Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 9)

Symbol	Parameter		Min	Max	Unit
V _{CC}	Operating Voltage	Operating	1.65	5.5	V
		Data Retention Only	1.5	—	
V _I	Input Voltage		0	5.5	V
V _O	Output Voltage Active Mode		0	V _{CC}	V
	Output Voltage Power-Down Mode		0	5.5	
I _{OH}	High-Level Output Current	V _{CC} = 1.65V	—	-4	mA
		V _{CC} = 2.3V	—	-8	
		V _{CC} = 2.7V	—	-12	
		V _{CC} = 3.0V	—	-16	
		V _{CC} = 4.5V	—	-24	
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	—	4	mA
		V _{CC} = 2.3V	—	8	
		V _{CC} = 2.7V	—	12	
		V _{CC} = 3.0V	—	16	
		V _{CC} = 4.5V	—	24	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 1.65V to 2.7V	—	20	ns/V
		V _{CC} = 2.7V to 5.5V	—	10	
T _A	Operating Free-Air Temperature		-40	+125	°C

Note: 9. Unused inputs should be held at V_{CC} or Ground.

Electrical Characteristics (All typical values are at $T_A = +25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	V_{CC}	-40°C to +85°C			-40°C to +125°C		Unit
				Min	Typ.	Max	Min	Max	
V_{IH}	High-Level Input Voltage	—	$V_{CC} = 1.65\text{V to } 1.95\text{V}$	$0.65 \times V_{CC}$	—	—	$0.65 \times V_{CC}$	—	V
			$V_{CC} = 2.3\text{V to } 2.7\text{V}$	1.7	—	—	1.7	—	
			$V_{CC} = 2.7\text{V to } 3.6\text{V}$	2.0	—	—	2.0	—	
			$V_{CC} = 4.5\text{V to } 5.5\text{V}$	$0.7 \times V_{CC}$	—	—	$0.7 \times V_{CC}$	—	
V_{IL}	Low-Level Input Voltage	—	$V_{CC} = 1.65\text{V to } 1.95\text{V}$	—	—	$0.35 \times V_{CC}$	—	$0.35 \times V_{CC}$	V
			$V_{CC} = 2.3\text{V to } 2.7\text{V}$	—	—	0.7	—	0.7	
			$V_{CC} = 2.7\text{V to } 3.6\text{V}$	—	—	0.8	—	0.8	
			$V_{CC} = 4.5\text{V to } 5.5\text{V}$	—	—	$0.3 \times V_{CC}$	—	$0.3 \times V_{CC}$	
V_{OH}	High-Level Output Voltage	$I_{OH} = -100\mu\text{A}$	1.65V to 5.5V	$V_{CC} - 0.1$	V_{CC}	—	$V_{CC} - 0.1$	—	V
		$I_{OH} = -4\text{mA}$	1.65V	1.2	1.53	—	0.95	—	
		$I_{OH} = -8\text{mA}$	2.3V	1.9	2.13	—	1.7	—	
		$I_{OH} = -12\text{mA}$	2.7	2.2	2.5	—	1.9	—	
		$I_{OH} = -16\text{mA}$	3V	2.4	2.7	—	2.2	—	
		$I_{OH} = -24\text{mA}$		2.3	2.6	—	2.0	—	
		$I_{OH} = -32\text{mA}$	4.5V	3.8	4.1	—	3.4	—	
V_{OL}	Low-Level Output Voltage	$I_{OL} = 100\mu\text{A}$	1.65V to 5.5V	—	0	0.1	—	0.1	V
		$I_{OL} = 4\text{mA}$	1.65V	—	0.08	0.45	—	0.7	
		$I_{OL} = 8\text{mA}$	2.3V	—	0.14	0.3	—	0.45	
		$I_{OL} = 12\text{mA}$	2.7V	—	0.19	0.4	—	0.6	
		$I_{OL} = 16\text{mA}$	3V	—	0.25	0.4	—	0.6	
		$I_{OL} = 24\text{mA}$		—	0.37	0.55	—	0.8	
		$I_{OL} = 32\text{mA}$	4.5V	—	0.43	0.55	—	0.8	
I_I	Input Current	$V_I = 5.5\text{V or GND}$	0V to 5.5V	—	± 0.1	± 5	—	± 20	μA
I_{OZ}	Z-State Leakage Current	$V_I = V_{IH} \text{ or } V_{IL}$ $V_O = 5.5\text{V or GND}$	3.6V	—	± 0.1	± 10	—	± 20	μA
I_{OFF}	Power Down Leakage Current	$V_I \text{ or } V_O = 5.5\text{V}$	0V	—	± 0.1	± 10	—	± 20	μA
I_{CC}	Supply Current	$V_I = 5.5\text{V or GND}$ $I_O = 0\text{A}$	1.65V to 5.5V	—	0.1	10	—	40	μA
ΔI_{CC}	Additional Supply Current	One input at $V_{CC} - 0.6\text{V}$ Other inputs at V_{CC} or GND	2.3V to 5.5V	—	5	500	—	5,000	μA
C_I	Input Capacitance	$V_I = V_{CC} \text{ or } \text{GND}$	3.3V	—	2.5	—	—	—	pF

Operating Characteristics

Parameter	Test Conditions	V _{CC} = 1.8V	V _{CC} = 2.5V	V _{CC} = 3.3V	V _{CC} = 5V	Unit
		Typ.	Typ.	Typ.	Typ.	
C _{pd}	f = 10MHz output enabled	17	17	17	17	pF
	f = 10MHz output disabled	5	5	5	5	pF

Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Typ.	Max	Unit
θ _{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN2010-8	(Note 10)	—	313	—	°C/W
		X2-DFN1410-8		—	321	—	
		X2-DFN1210-8		—	395	—	
θ _{JC}	Thermal Resistance Junction-to-Case	X2-DFN2010-8	(Note 10)	—	145	—	°C/W
		X2-DFN1410-8		—	166	—	
		X2-DFN1210-8		—	236	—	

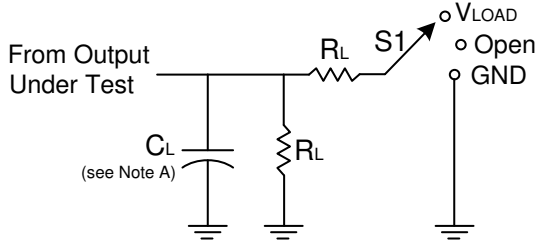
Note: 10. Test condition for each package type: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

Typical Values at T_A = +25°C and nominal voltages 1.8V, 2.5V, 2.7V, 3.3V, and 5.0V. See Figure 1.

Parameter	From Input	To Output	V _{CC}	T _A = -40°C to +85°C			T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t _{pd}	A	Y	1.8V ± 0.15V	1.0	3.9	9.8	1.0	12.3	ns
			2.5V ± 0.2V	0.5	2.6	4.9	0.5	6.3	
			2.7V	1.0	2.8	4.7	1.0	5.9	
			3.3V ± 0.3V	0.5	2.4	4.4	0.5	5.4	
			5.0V ± 0.5V	0.5	1.9	3.9	0.5	4.0	
t _{en}	OE	Y	1.8V ± 0.15V	1.0	4.1	10.0	1.0	12.5	ns
			2.5V ± 0.2V	1.0	2.6	5.0	1.0	6.3	
			2.7V	1.0	2.8	4.7	1.0	5.9	
			3.3V ± 0.3V	1.0	2.4	4.1	1.0	5.1	
			5.0V ± 0.5V	0.5	1.8	3.4	0.5	3.9	
t _{dis}	OE	Y	1.8V ± 0.15V	1.0	3.3	12.6	1.0	15.4	ns
			2.5V ± 0.2V	0.5	1.9	5.7	0.5	7.5	
			2.7V	1.5	3.0	4.8	1.5	6.2	
			3.3V ± 0.3V	1.0	2.5	4.4	1.0	5.7	
			5.0V ± 0.5V	0.5	1.8	3.3	0.5	4.4	

Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	Inputs		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8V \pm 0.15V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	1k Ω	0.15V
$2.5V \pm 0.2V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	500 Ω	0.15V
2.7V	2.7V	$\leq 2.5ns$	1.5V	6V	50pF	500 Ω	0.3V
$3.3V \pm 0.3V$	3V	$\leq 2.5ns$	1.5V	6V	50pF	500 Ω	0.3V
$5V \pm 0.5V$	V_{CC}	$\leq 2.5ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	500 Ω	0.3V

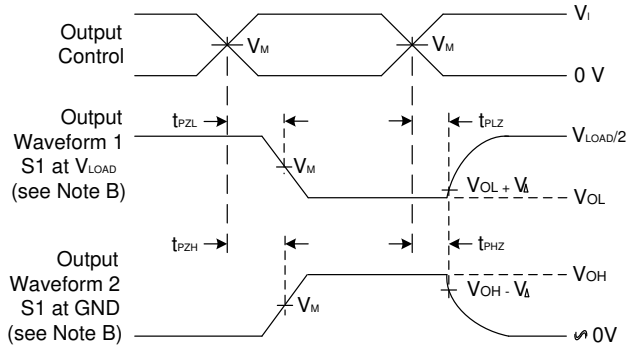
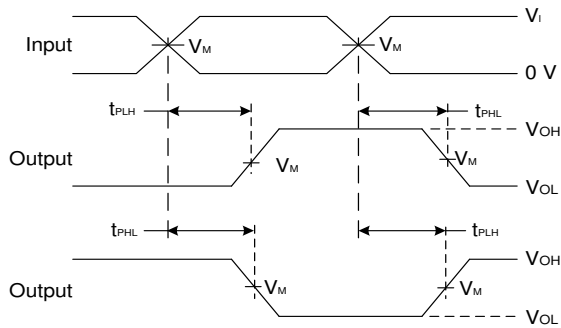
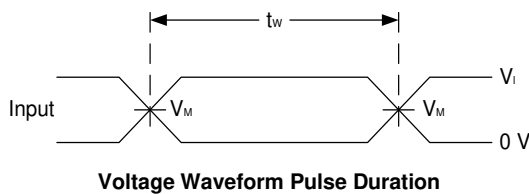
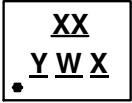


Figure 1. Load Circuit and Voltage Waveforms

- Notes:
- A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate $\leq 10MHz$.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - E. t_{PZL} and t_{PZH} are the same as t_{en} .
 - F. t_{PLH} and t_{PHL} are the same as t_{pd} .

Marking Information

(Top View)



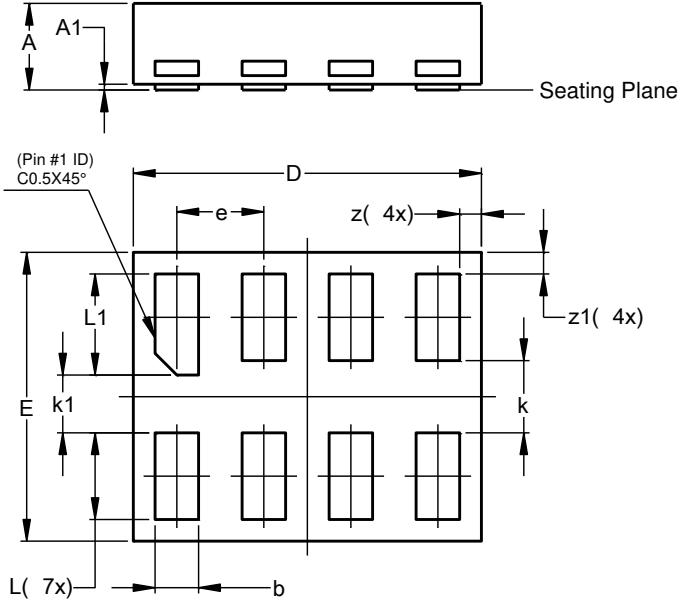
XX : Identification Code
Y : Year : 0~9
W : Week : A~Z : 1~26 week;
a~z : 27~52 week; z represents
52 and 53 week
X : Internal Code

Part Number	Package	Identification Code
74LVC2G126HD4-7	X2-DFN2010-8	9X
74LVC2G126HK3-7	X2-DFN1410-8	9Y
74LVC2G126RA3-7	X2-DFN1210-8	9Z

X2-DFN1210-8 Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1210-8

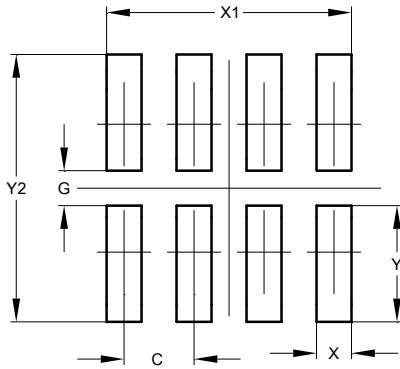


X2-DFN1210-8			
Dim	Min	Max	Typ
A	-	0.35	0.30
A1	0	0.03	0.02
b	0.10	0.20	0.15
D	1.15	1.25	1.20
E	0.95	1.05	1.00
e	-	-	0.30
k	-	-	0.25
k1	-	-	0.20
L	0.25	0.35	0.30
L1	0.30	0.40	0.35
z	0.050	0.100	0.075
z1	0.050	0.100	0.075
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1210-8

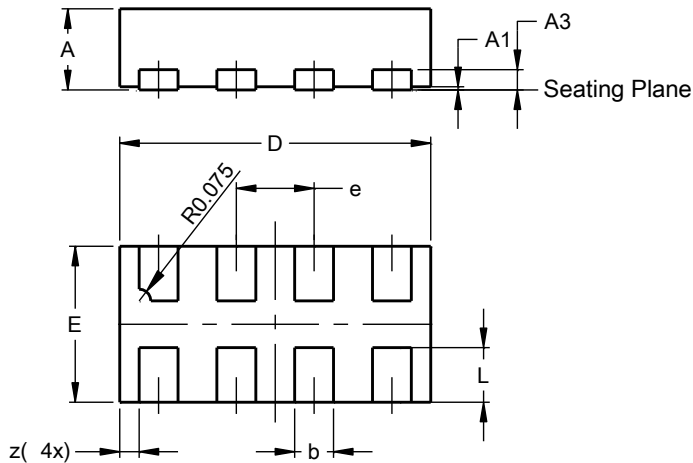


Dimensions	Value (in mm)
C	0.300
G	0.150
X	0.150
X1	1.050
Y	0.500
Y1	1.150

X2-DFN2010-8 Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN2010-8

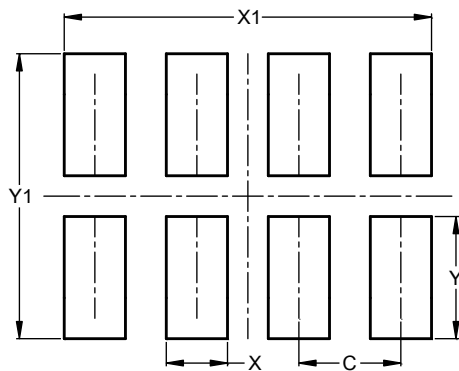


X2-DFN2010-8			
Dim	Min	Max	Typ
A	--	0.40	--
A1	0.00	0.05	0.02
A3	--	--	0.13
b	0.20	0.30	0.25
D	1.950	2.05	2.00
E	0.95	1.05	1.00
e	--	--	0.50
L	0.30	0.40	0.35
z	--	--	0.125
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN2010-8



Dimensions	Value (in mm)
C	0.500
X	0.300
X1	1.800
Y	0.600
Y1	1.400

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